162162

Abstract

Field-effect transistor structure, associated semiconductor memory cell and associated fabrication method

The invention relates to a field-effect transistor structure, an associated semiconductor memory cell and an associated fabrication method, in which case in order to realize a diode (D) a diode doping region (4) is formed in a semiconductor substrate (1) with a field-effect transistor structure (S/D, 3, K) and an electrically conductive diode connection layer (5) connects a control layer (3) of the field-effect transistor structure to the diode doping region (4). In this way, it is possible to deplete excess charge carriers (L) in the semiconductor substrate (1), thereby preventing an undesirable body effect.

Figure 5

G00002